

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <small>(use as many sheets as necessary)</small>				<i>Complete If Known</i>		
				Application Number	10 / 765, 804	
				Filing Date	1-27-04	
				First Named Inventor	Paul A. Ingersoll	
				Group Art Unit	2823	
				Examiner Name	B. KERBEDZ	
				Attorney Docket Number	SC13113TP	
<b>U. S. PATENT DOCUMENTS</b>						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number -Kind Code <sup>2</sup> (if known)				
BK	AA	US -6,611,019 B2	08-26-2003	RUDECK		
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<b>FOREIGN PATENT DOCUMENTS</b>						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
<b>NON PATENT LITERATURE DOCUMENTS</b>						
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T <sup>2</sup>
BK	AE	WATANABE et al., "An Advanced Technique for Fabricating Hemispherical-Grained (HSG) Silicon Storage Electrodes," IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 42, NO. 2, FEBRUARY 1995, pp. 295-300.				
BN	AF	DE BLAUWE et al., "A Novel, Aerosol-Nanocrystal Floating-Gate Device for Non-Volatile Memory Applications," IEEE, pp. 29.7.1 - 29.7.4 (2000).				

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<sup>1</sup> Unique citation designation number. <sup>2</sup> See Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English Language Translation is attached.